



STP14NF12 STP14NF12FP

N-CHANNEL 120V - 0.16Ω - 14A TO-220/TO-220FP
LOW GATE CHARGE STRIPFET™ POWER MOSFET

TYPE	V _{DSS}	R _{DS(on)}	I _D
STP14NF12	120 V	< 0.18 Ω	14 A
STP14NF12FP	120 V	< 0.18 Ω	14 A

- TYPICAL R_{DS(on)} = 0.16Ω
- EXCEPTIONAL dv/dt CAPABILITY
- APPLICATION ORIENTED CHARACTERIZATION

DESCRIPTION

This Power MOSFET series realized with STMicroelectronics unique STRIPFET process has specifically been designed to minimize input capacitance and gate charge. It is therefore suitable as primary switch in advanced high-efficiency isolated DC-DC converters for Telecom and Computer application. It is also intended for any application with low gate charge drive requirements

APPLICATIONS

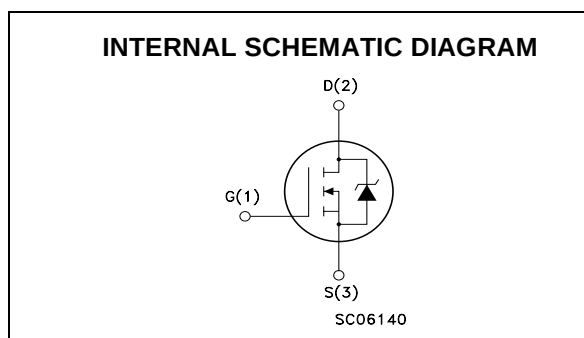
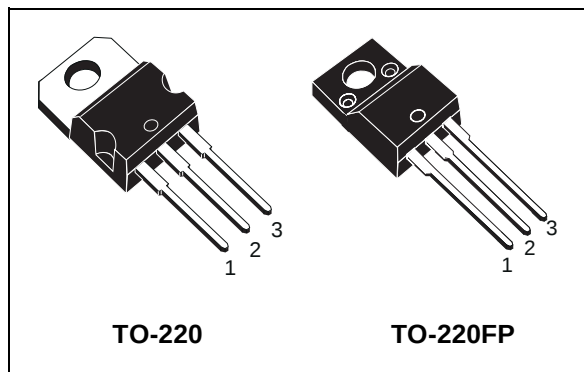
- HIGH-EFFICIENCY DC-DC CONVERTERS
- UPS AND MOTOR CONTROL

ABSOLUTE MAXIMUM RATINGS

Symbol	Parameter	Value		Unit
		STP14NF12	STP14NF12FP	
V _{DS}	Drain-source Voltage (V _{GS} = 0)	120		V
V _{DGR}	Drain-gate Voltage (R _{GS} = 20 kΩ)	120		V
V _{GS}	Gate- source Voltage	±20		V
I _D	Drain Current (continuous) at T _C = 25°C	14	8.5	A
I _D	Drain Current (continuous) at T _C = 100°C	9	6	A
I _{DM} (●)	Drain Current (pulsed)	56	34	A
P _{TOT}	Total Dissipation at T _C = 25°C	60	25	W
	Derating Factor	0.4	0.17	W/°C
dv/dt (1)	Peak Diode Recovery voltage slope	9		V/ns
E _{AS} (2)	Single Pulse Avalanche Energy	60		mJ
V _{ISO}	Insulation Withstand Voltage (DC)	-	2500	V
T _j	Operating Junction Temperature	-55 to 175		°C
T _{stg}	Storage Temperature			

(●) Pulse width limited by safe operating area

(1) I_{SD} ≤ 14A, di/dt ≤ 300A/μs, V_{DD} ≤ V_{(BR)DSS}, T_j ≤ T_{JMAX}.
(2) Starting T_j = 25°C, I_D = 14A, V_{DD} = 50V



STP14NF12/STP14NF12FP

THERMAL DATA

		TO-220	TO-220FP	
R _{thj-case}	Thermal Resistance Junction-case Max	2.5	6	°C/W
R _{thj-amb}	Thermal Resistance Junction-ambient Max	62.5		°C/W
T _I	Maximum Lead Temperature For Soldering Purpose	300		°C

ELECTRICAL CHARACTERISTICS (T_{CASE} = 25 °C UNLESS OTHERWISE SPECIFIED)

OFF

Symbol	Parameter	Test Conditions	Min.	Typ.	Max.	Unit
V _{(BR)DSS}	Drain-source Breakdown Voltage	I _D = 250 µA, V _{GS} = 0	120			V
I _{DSS}	Zero Gate Voltage Drain Current (V _{GS} = 0)	V _{DS} = Max Rating V _{DS} = Max Rating, T _C = 125 °C			1 10	µA µA
I _{GSS}	Gate-body Leakage Current (V _{DS} = 0)	V _{GS} = ±20V			±100	nA

ON (1)

Symbol	Parameter	Test Conditions	Min.	Typ.	Max.	Unit
V _{GS(th)}	Gate Threshold Voltage	V _{DS} = V _{GS} , I _D = 250µA	2	3	4	V
R _{DS(on)}	Static Drain-source On Resistance	V _{GS} = 10V, I _D = 7 A		0.16	0.18	Ω

DYNAMIC

Symbol	Parameter	Test Conditions	Min.	Typ.	Max.	Unit
g _{fs} (1)	Forward Transconductance	V _{DS} = 15V, I _D = 7 A		4		S
C _{iss}	Input Capacitance	V _{DS} = 25V, f = 1 MHz, V _{GS} = 0		460		pF
C _{oss}	Output Capacitance			70		pF
C _{rss}	Reverse Transfer Capacitance			30		pF

ELECTRICAL CHARACTERISTICS (CONTINUED)**SWITCHING ON**

Symbol	Parameter	Test Conditions	Min.	Typ.	Max.	Unit
$t_{d(on)}$	Turn-on Delay Time	$V_{DD} = 50\text{ V}$, $I_D = 7\text{ A}$		16		ns
t_r	Rise Time	$R_G = 4.7\Omega$, $V_{GS} = 10\text{ V}$ (Resistive Load, see Figure 3)		25		ns
Q_g	Total Gate Charge	$V_{DD} = 80\text{ V}$, $I_D = 14\text{ A}$,		15.5	21	nC
Q_{gs}	Gate-Source Charge	$V_{GS} = 10\text{ V}$		3.7		nC
Q_{gd}	Gate-Drain Charge			4.7		nC

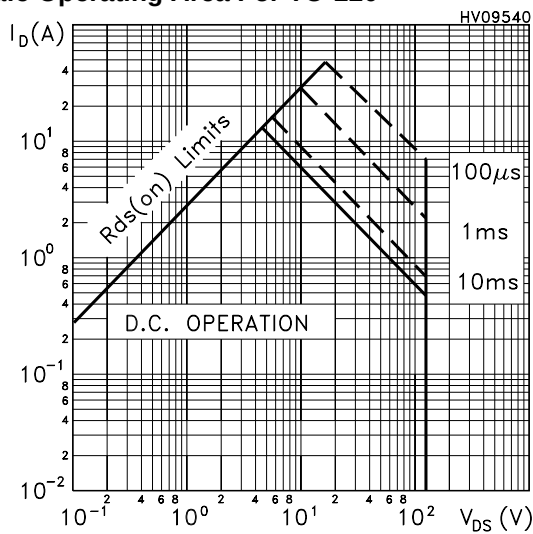
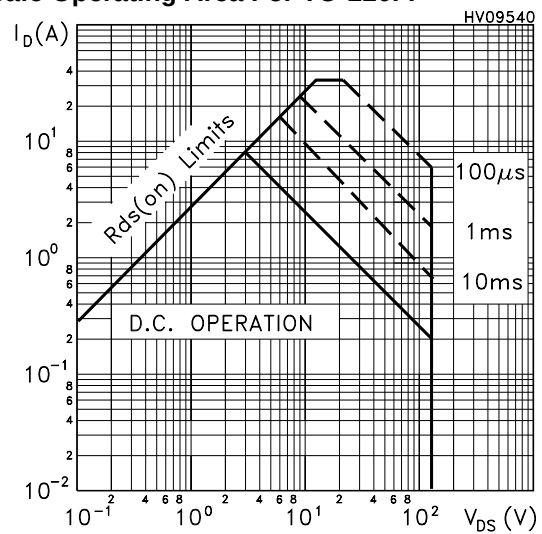
SWITCHING OFF

Symbol	Parameter	Test Conditions	Min.	Typ.	Max.	Unit
$t_{d(off)}$	Turn-off-Delay Time	$V_{DD} = 50\text{ V}$, $I_D = 7\text{ A}$,		32		ns
t_f	Fall Time	$R_G = 4.7\Omega$, $V_{GS} = 10\text{ V}$ (Resistive Load, see Figure 3)		8		ns

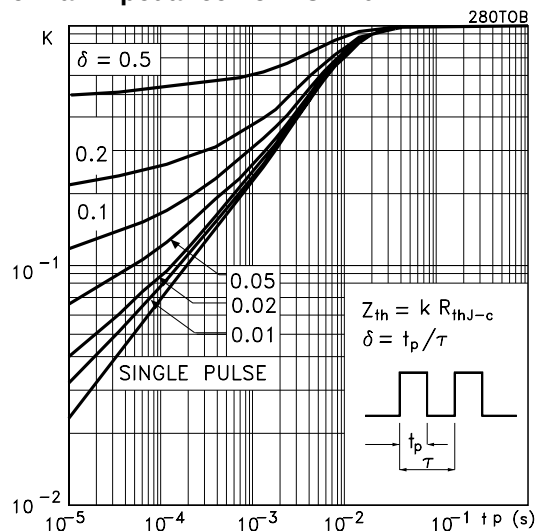
SOURCE DRAIN DIODE

Symbol	Parameter	Test Conditions	Min.	Typ.	Max.	Unit
I_{SD}	Source-drain Current				14	A
$I_{SDM(2)}$	Source-drain Current (pulsed)				56	A
$V_{SD(1)}$	Forward On Voltage	$I_{SD} = 14\text{ A}$, $V_{GS} = 0$			1.5	V
t_{rr}	Reverse Recovery Time	$I_{SD} = 14\text{ A}$, $di/dt = 100\text{ A}/\mu\text{s}$,		92		ns
Q_{rr}	Reverse Recovery Charge	$V_{DD} = 50\text{ V}$, $T_j = 150^\circ\text{C}$		230		nC
I_{RRM}	Reverse Recovery Current	(see test circuit, Figure 5)		5		A

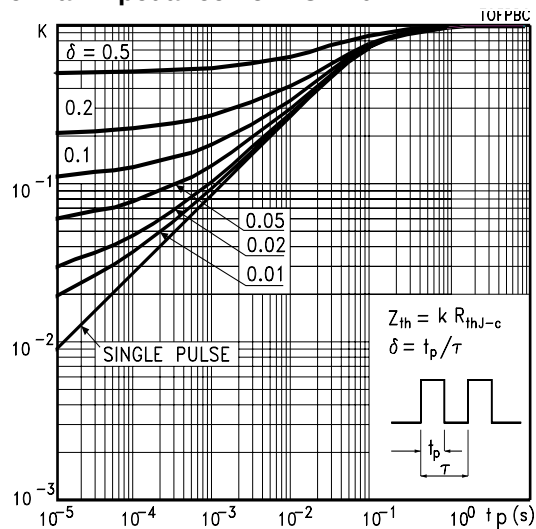
Note: 1. Pulsed: Pulse duration = 300 μs , duty cycle 1.5 %.
 2. Pulse width limited by safe operating area.

Safe Operating Area For TO-220**Safe Operating Area For TO-220FP**

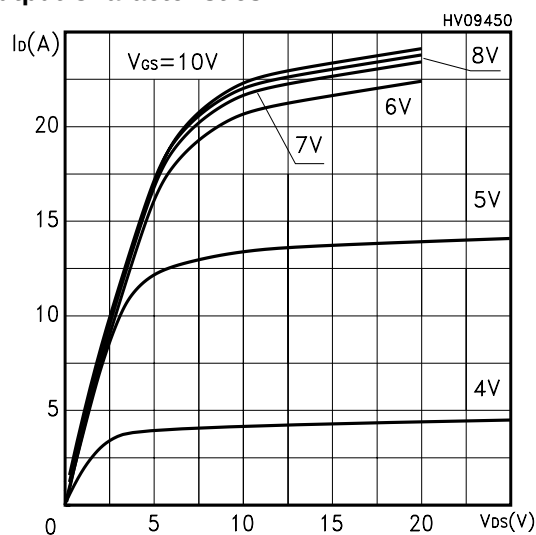
Thermal Impedance For TO-220



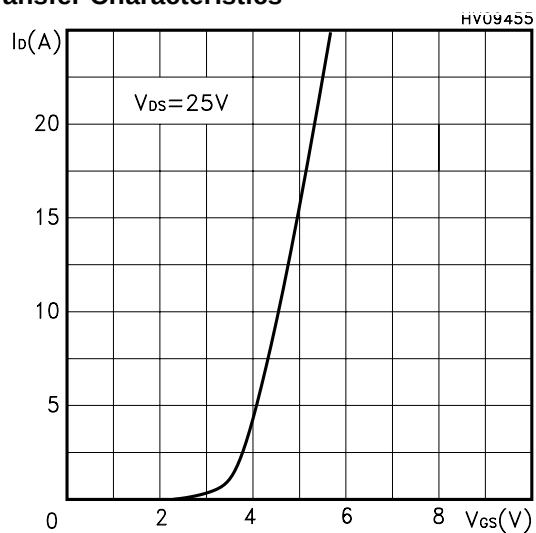
Thermal Impedance For TO-220FP



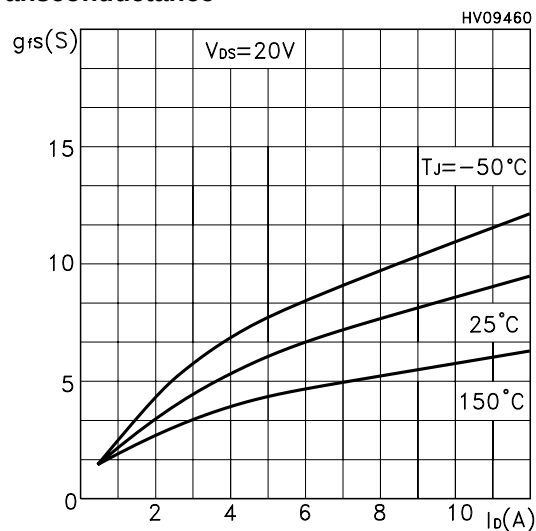
Output Characteristics



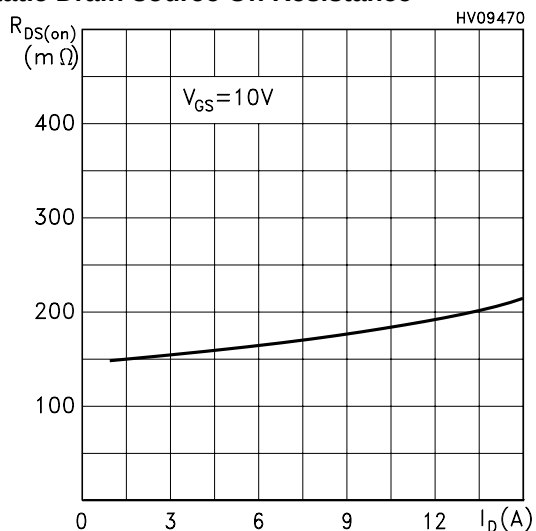
Transfer Characteristics



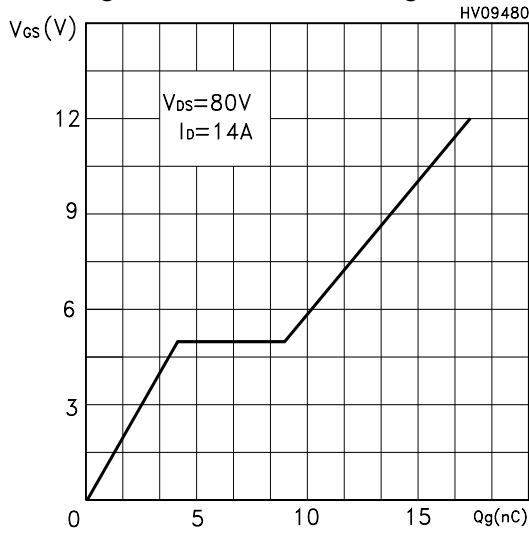
Transconductance



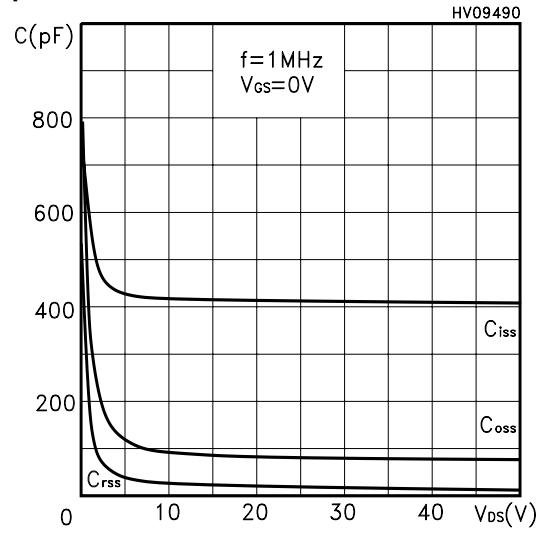
Static Drain-source On Resistance



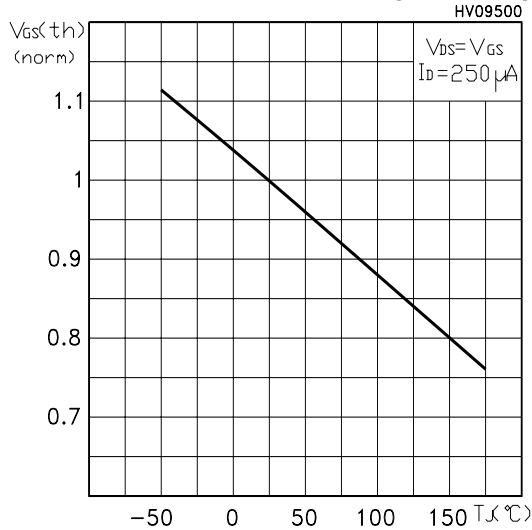
Gate Charge vs Gate-source Voltage



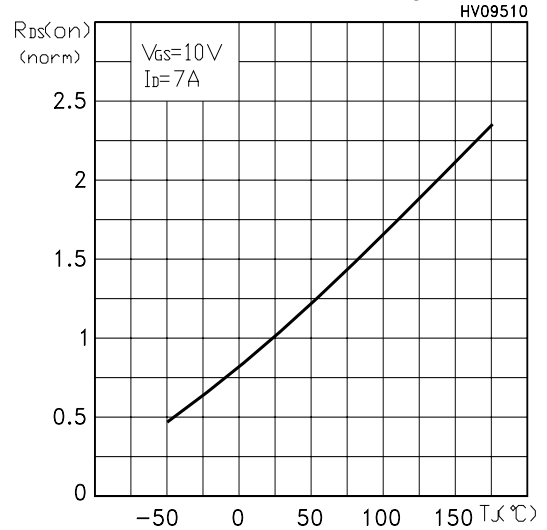
Capacitance Variations



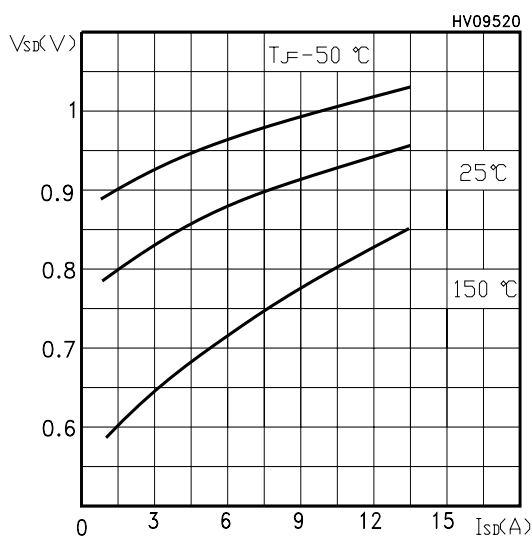
Normalized Gate Threshold Voltage vs Temp.



Normalized On Resistance vs Temperature



Source-drain Diode Forward Characteristics



Normalized BVDSS vs Temperature

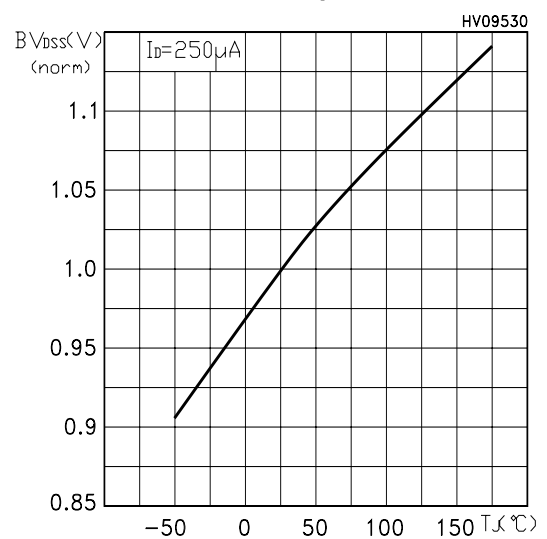


Fig. 1: Unclamped Inductive Load Test Circuit

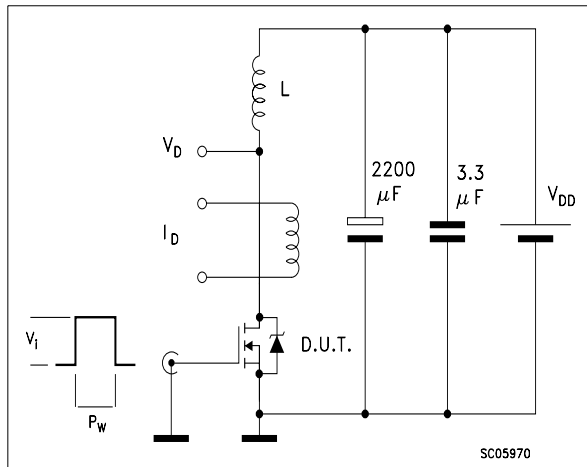


Fig. 2: Unclamped Inductive Waveform

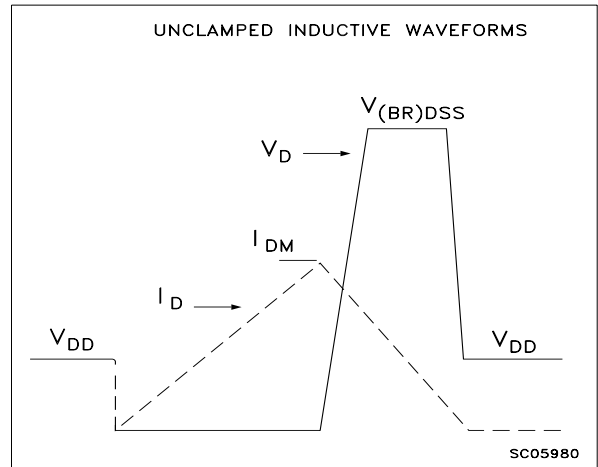


Fig. 3: Switching Times Test Circuit For Resistive Load

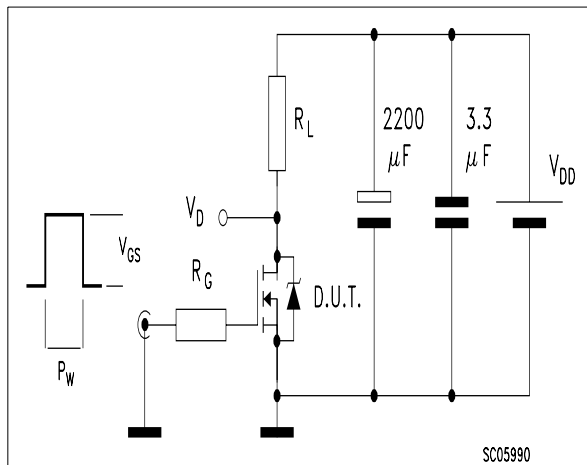


Fig. 4: Gate Charge test Circuit

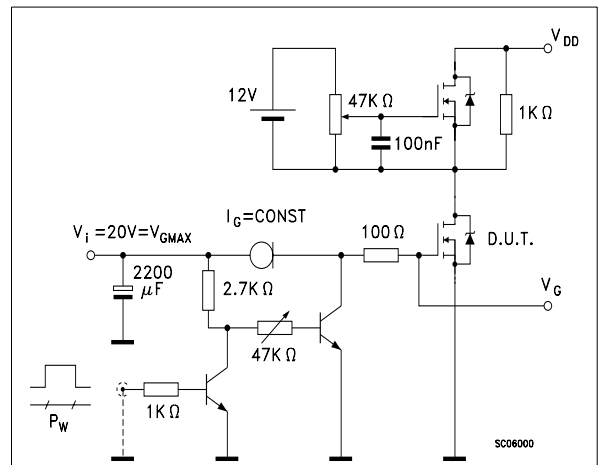
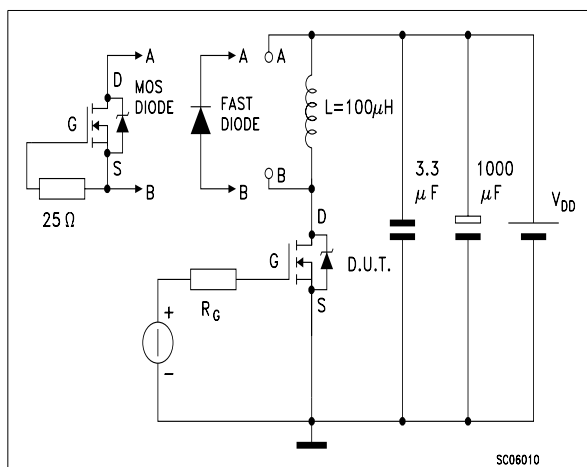
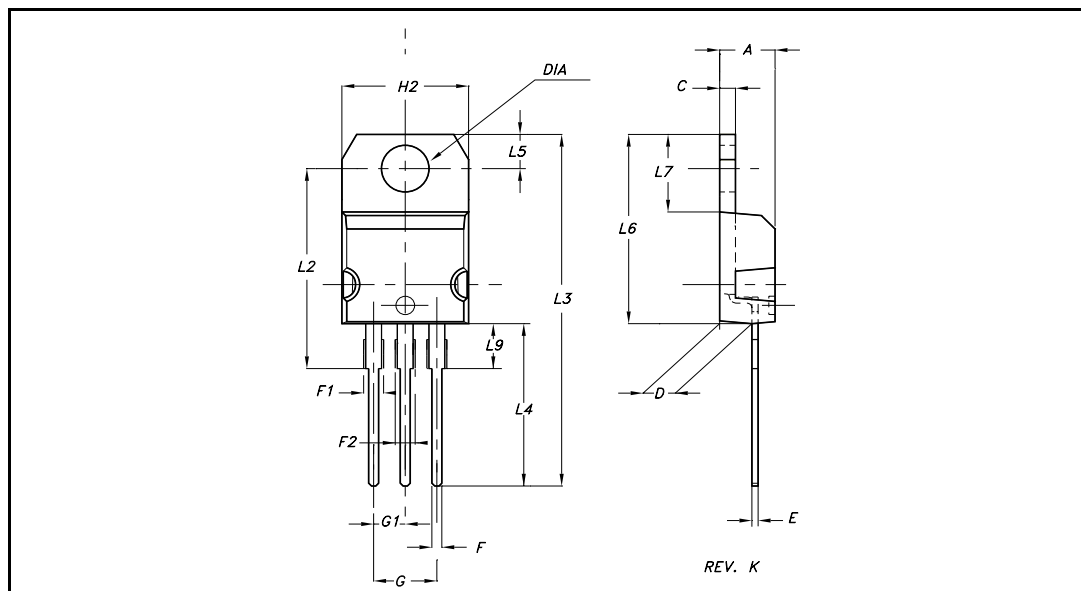


Fig. 5: Test Circuit For Inductive Load Switching And Diode Recovery Times



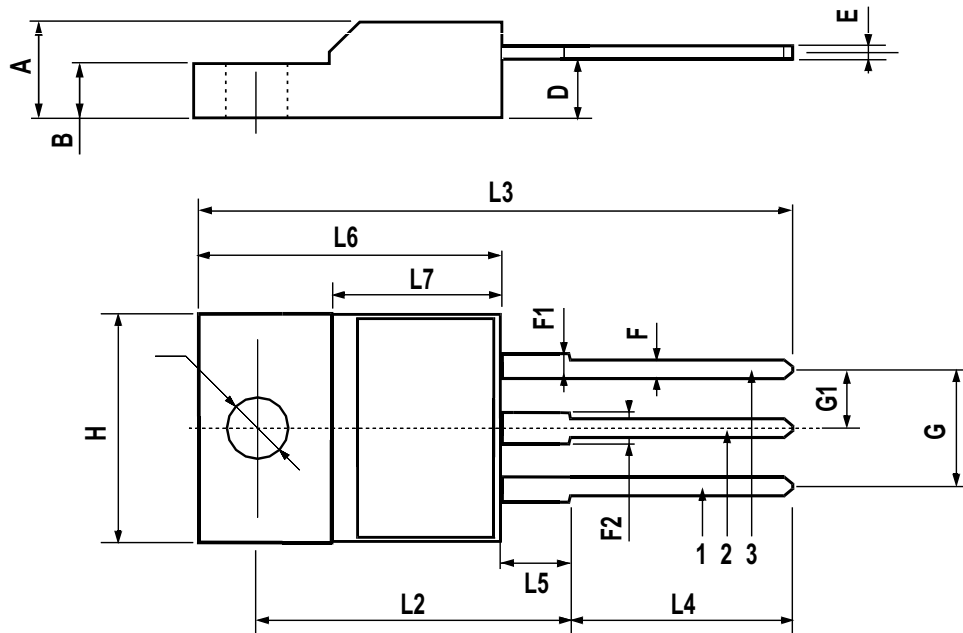
TO-220 MECHANICAL DATA

DIM.	mm.			inch		
	MIN.	TYP	MAX.	MIN.	TYP.	MAX.
A	4.40		4.60	0.173		0.181
C	1.23		1.32	0.048		0.051
D	2.40		2.72	0.094		0.107
E	0.49		0.70	0.019		0.027
F	0.61		0.88	0.024		0.034
F1	1.14		1.70	0.044		0.066
F2	1.14		1.70	0.044		0.066
G	4.95		5.15	0.194		0.202
G1	2.40		2.70	0.094		0.106
H2	10		10.40	0.393		0.409
L2		16.40			0.645	
L3		28.90			1.137	
L4	13		14	0.511		0.551
L5	2.65		2.95	0.104		0.116
L6	15.25		15.75	0.600		0.620
L7	6.20		6.60	0.244		0.259
L9	3.50		3.93	0.137		0.154
DIA	3.75		3.85	0.147		0.151



TO-220FP MECHANICAL DATA

DIM.	mm.			inch		
	MIN.	TYP	MAX.	MIN.	TYP.	MAX.
A	4.4		4.6	0.173		0.181
B	2.5		2.7	0.098		0.106
D	2.5		2.75	0.098		0.108
E	0.45		0.7	0.017		0.027
F	0.75		1	0.030		0.039
F1	1.15		1.7	0.045		0.067
F2	1.15		1.7	0.045		0.067
G	4.95		5.2	0.195		0.204
G1	2.4		2.7	0.094		0.106
H	10		10.4	0.393		0.409
L2		16			0.630	
L3	28.6		30.6	1.126		1.204
L4	9.8		10.6	.0385		0.417
L5	2.9		3.6	0.114		0.141
L6	15.9		16.4	0.626		0.645
L7	9		9.3	0.354		0.366
Ø	3		3.2	0.118		0.126



Information furnished is believed to be accurate and reliable. However, STMicroelectronics assumes no responsibility for the consequences of use of such information nor for any infringement of patents or other rights of third parties which may result from its use. No license is granted by implication or otherwise under any patent or patent rights of STMicroelectronics. Specifications mentioned in this publication are subject to change without notice. This publication supersedes and replaces all information previously supplied. STMicroelectronics products are not authorized for use as critical components in life support devices or systems without express written approval of STMicroelectronics.

© The ST logo is a registered trademark of STMicroelectronics

© 2002 STMicroelectronics - Printed in Italy - All Rights Reserved
STMicroelectronics GROUP OF COMPANIES

Australia - Brazil - Canada - China - Finland - France - Germany - Hong Kong - India - Israel - Italy - Japan - Malaysia - Malta - Morocco
Singapore - Spain - Sweden - Switzerland - United Kingdom - United States.

© <http://www.st.com>